

# Dual Drive 10Gb/s LN Modulator with Monitor PD

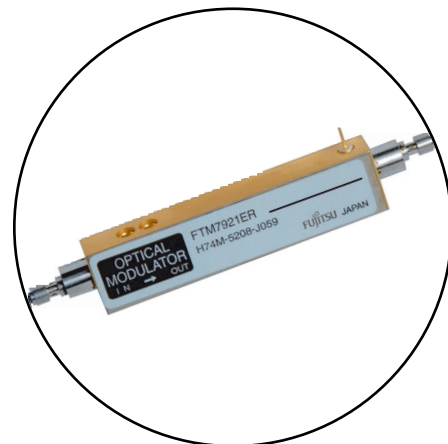
# FTM7921ER

## FEATURES

- Z-Cut Design Supports Low Drive Voltages
- Zero Chirp Differential Input Design
- Integrated Monitor Photodiode
- GPO RF Input Connectors

## DESCRIPTION

The FTM7921ER is a Ti:LiNbO<sub>3</sub> Dual Drive Mach-Zehnder modulator with a modulation speed of up to 10.7 Gb/s. This optical modulator integrates a monitor PD chip and coupler function for the automatic bias control (ABC) to compensate for DC-drift and other phenomena.



## ABSOLUTE MAXIMUM RATINGS (Tc=25°C, Unless otherwise specified)

| Parameter                   | Symbol               | Condition | Limits |      |      | Unit |
|-----------------------------|----------------------|-----------|--------|------|------|------|
|                             |                      |           | Min.   | Typ. | Max. |      |
| Storage Temperature         | T <sub>stg</sub>     | Ambient   | -40    | -    | 85   | °C   |
| Operating Case Temperature  | T <sub>op</sub>      | Case      | -5     | -    | 70   | °C   |
| Storage Relative Humidity   | RH <sub>stg</sub>    |           | 5      | -    | 95   | %    |
| Operating Relative Humidity | RH <sub>op</sub>     |           | 5      | -    | 85   | %    |
| DC Input Voltage            | V <sub>in(DC)</sub>  |           | -      | -    | ±16  | V    |
| Optical Input Power         | P <sub>in(opt)</sub> |           | -      | -    | 50   | mW   |
| Monitor PD Reverse Voltage  | V <sub>RM</sub>      |           | -      | -    | 20   | V    |
| Monitor PD Reverse Current  | I <sub>RM</sub>      |           | -      | -    | 1    | mA   |
| Monitor PD Forward Current  | I <sub>FM</sub>      |           | -      | -    | 3    | mA   |

## ELECTRICAL CHARACTERISTICS (Tc =-5 ~ 70°C, 25 years Unless otherwise specified)

| Parameter          | Symbol            | Condition   | Limit |      |      | Unit |
|--------------------|-------------------|---|-------|------|------|------|
|                    |                   |   | Min.  | Typ. | Max. |      |
| Operating Bit Rate | -                 |   | 10.7  | -    | -    | Gb/s |
| Drive Voltage      | V <sub>π</sub>    | At 10.7 Gb/s,<br>Complementary Drive                        | -     | -    | 2.6  | V    |
| Drive Voltage      | V <sub>π</sub>    | At low frequency,<br>single drive,<br>and at each electrode | -     | -    | 4.0  | V    |
| DC Bias Voltage    | V <sub>Bias</sub> | Single Bias   | -15   | -    | 15   | V    |
| RF Input Impedance | Z <sub>in</sub>   | Internally Terminated                                       | 39    | 50   | -    | Ω    |
| RF Return Loss     | S <sub>11</sub>   | 130MHz ~ 5GHz   | 13    | -    | -    | dB   |
|                    |                   | 5GHz ~ 10GHz  | 10    | -    | -    |      |

OPTICAL SPECIFICATIONS (T<sub>c</sub>=-5 ~ 70°C, 25 years)

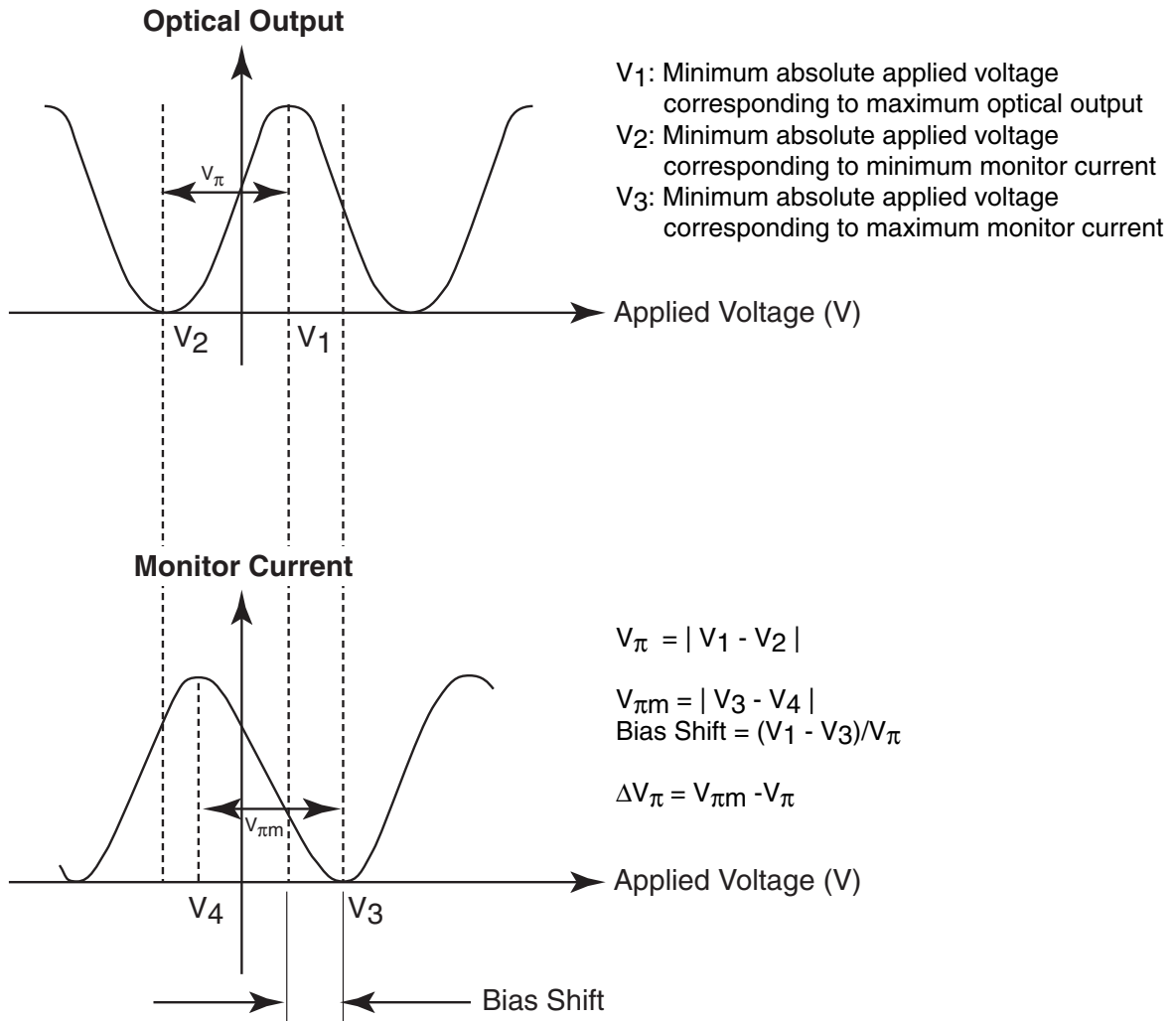
| Parameter               | Symbol           | Condition                                 | Limit |      |      | Unit |
|-------------------------|------------------|---|-------|------|------|------|
|                         |                  |   | Min.  | Typ. | Max. |      |
| Optical Bandwidth       | BW               | 3dB Down Relative to 130MHz, Small-signal | 8.5   | -    | -    | GHz  |
| Operating Wavelength    | $\lambda_{op}$   | C Band                                    | 1530  | -    | 1570 | nm   |
|                         |                  | L Band                                    | 1570  | -    | 1608 |      |
| On/Off Extinction Ratio | R <sub>ext</sub> | At Low Frequency                          | 18    | -    | -    | dB   |
|                         |                  | At 10.7Gb/s Complementary Drive           | 12    | -    | -    |      |
| Optical Return Loss     | ORL              | BOL, Input & Output                       | 35    | -    | -    | dB   |
|                         |                  | EOL, Input & Output                       | 30    | -    | -    |      |
| Optical Insertion Loss  | IL               | C Band, No Connector                      | -     | -    | 6.0  | dB   |
|                         |                  | L Band, No Connector                      | -     | -    | 7.0  |      |
| RF Input Timing Skew    | T <sub>skw</sub> |   | -2.5  | -    | +2.5 | ps   |
| Rise Time               | t <sub>r</sub>   | 20-80%                                    | -     | -    | 30   | ps   |
| Fall Time               | t <sub>f</sub>   | 10-90%                                    | -     | -    | 45   | ps   |
| Pulse Overshoot         | -                |   | -     | -    | 10   | %    |
| Pulse Undershoot        | -                |   | -     | -    | 10   | %    |
| Alpha Parameter         | $\alpha$         | Balanced Input                            | -0.2  | -    | +0.2 | -    |

ELECTRO-OPTICAL SPECIFICATIONS OF MONITOR PD (T<sub>c</sub>=-5 ~ 70°C, 25 years)

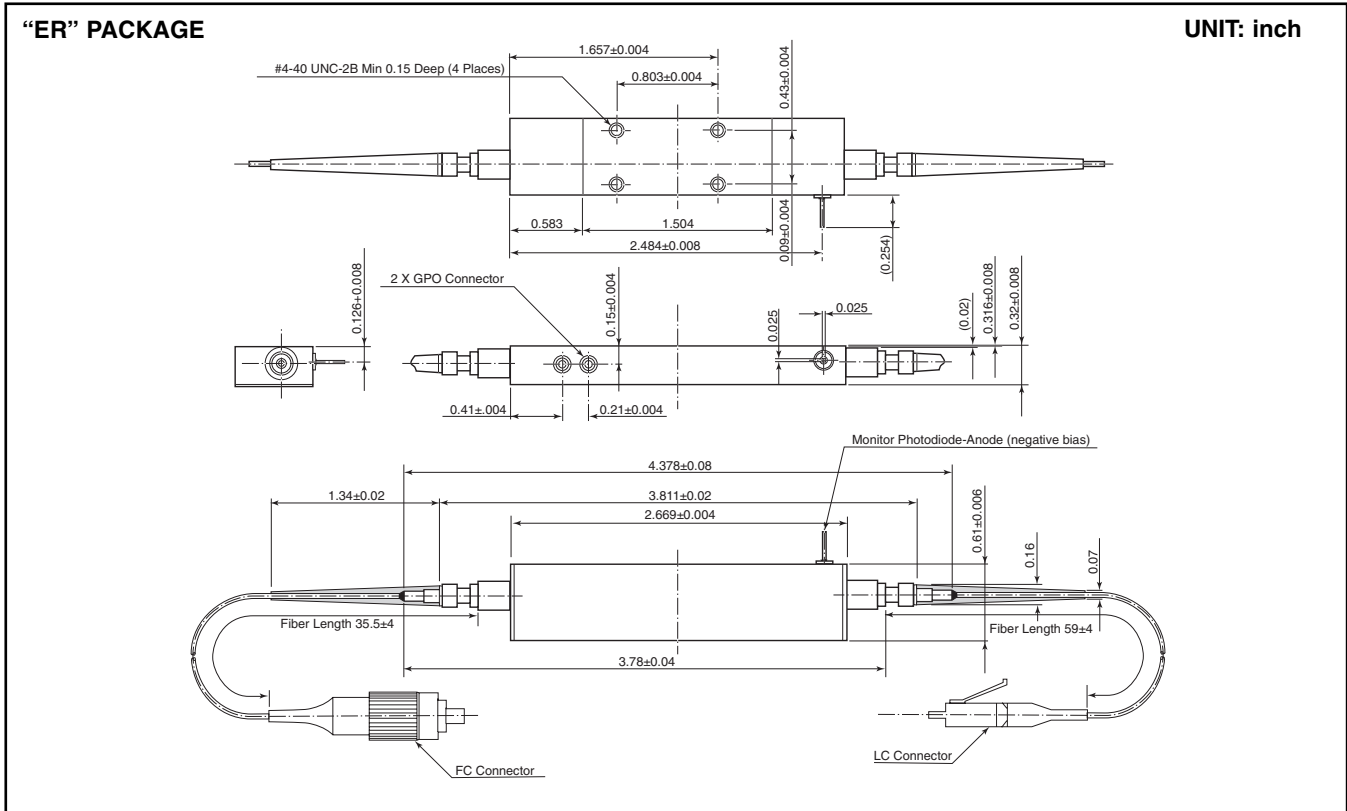
| Parameter                            | Symbol           | Condition                   | Limit  |      |       | Unit |
|--------------------------------------|------------------|-----------------------------|--------|------|-------|------|
|                                      |                  |                             | Min.   | Typ. | Max.  |      |
| Responsivity                         | R <sub>mAC</sub> | -                           | 0.0023 | -    | 0.022 | A/W  |
| Bias Shift                           | -                | Note (1)                    | -20    | -    | +20   | %    |
| Monitor PD V <sub>π</sub> Difference | $\Delta V_{\pi}$ | Difference at Low Frequency | -0.3   | -    | 0.3   | V    |

Note 1. Reference Table 1 for explanation

**Table 1**



Note: These measurements are performed at a low frequency of  $\leq 100\text{Hz}$ .



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